



Description

The HSSM3J351RLF uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

General Features

$V_{DS} = -60V, I_D = -3A$

$R_{DS(ON)} < 140m\Omega @ V_{GS} = -10V$

$R_{DS(ON)} < 190m\Omega @ V_{GS} = -4.5V$

Application

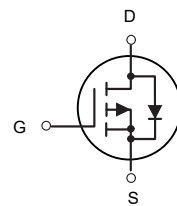
Battery protection

Load switch

Uninterruptible power supply



SOT-23-3L



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HSSM3J351RLF	SOT-23-3L	3P06	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	-3	A
I_{DM}	Drain Current-Pulsed (Note 1)	-6	A
P_D	Maximum Power Dissipation	1.5	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	85	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-60	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.049	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-3A	---	115	140	mΩ
		V _{GS} =-4.5V, I _D =-2A	---	---	190	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250μA	-1.0	---	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	5.42	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-48V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =-48V, V _{GS} =0V, T _J =150°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	5.8	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-20V, V _{GS} =-4.5V, I _D =-3A	---	5.9	---	nC
Q _{gs}	Gate-Source Charge		---	2.9	---	
Q _{gd}	Gate-Drain Charge		---	1.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-12V, V _{GS} =-10V, R _G =3.3Ω, I _D =-3A	---	10	---	ns
T _r	Rise Time		---	17	---	
T _{d(off)}	Turn-Off Delay Time		---	22	---	
T _f	Fall Time		---	21	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, F=1MHz	---	715	---	pF
C _{oss}	Output Capacitance		---	51	---	
C _{rss}	Reverse Transfer Capacitance		---	34	---	
I _s	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	-3	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	-6	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-20A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



P-Channel Typical Characteristics

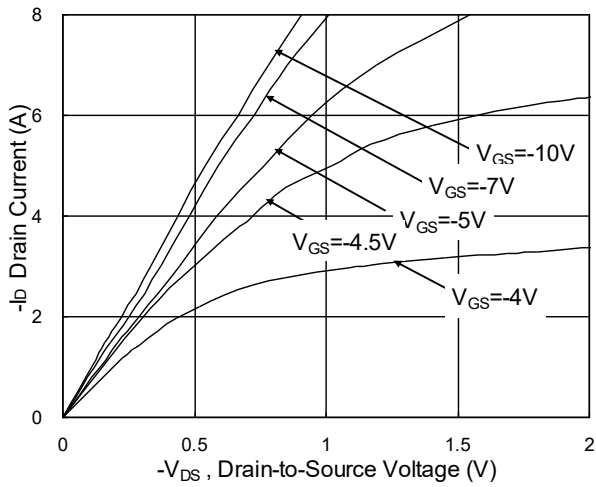


Fig.1 Typical Output Characteristics

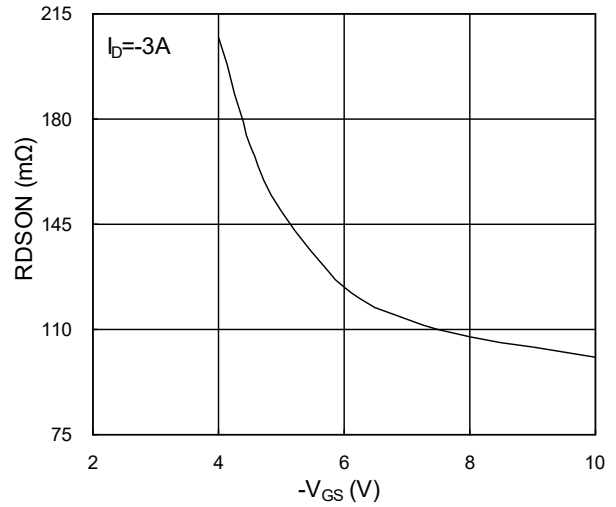


Fig.2 On-Resistance vs. G-S Voltage

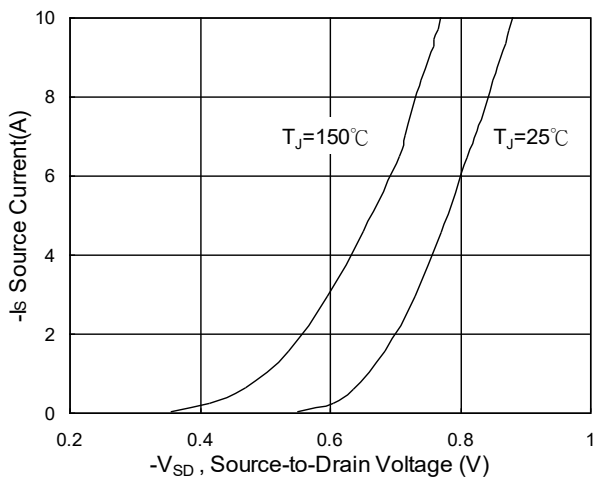


Fig.3 Forward Characteristics Of Reverse

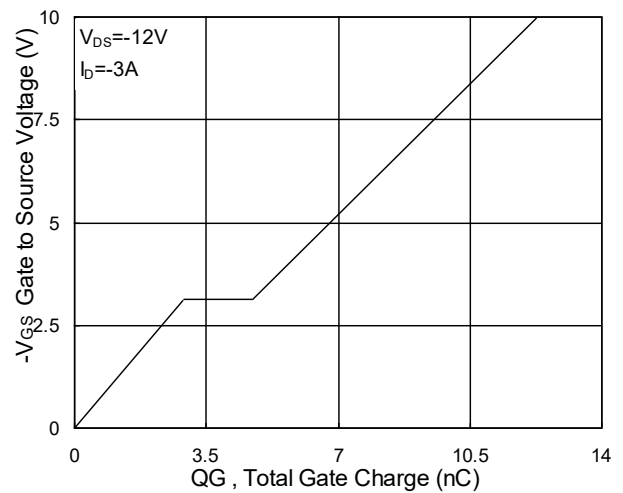


Fig.4 Gate-Charge Characteristics

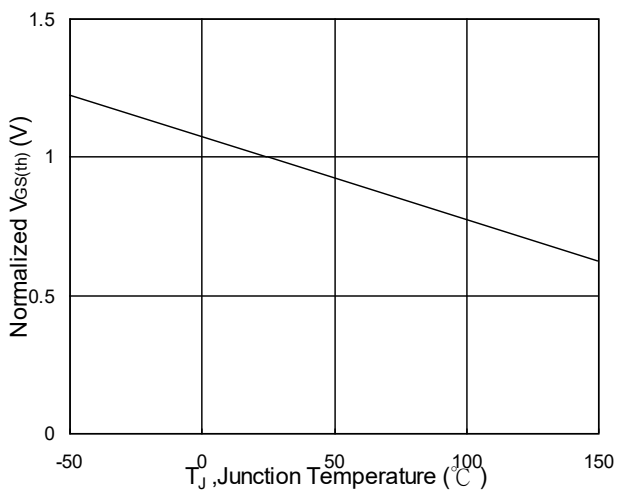


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

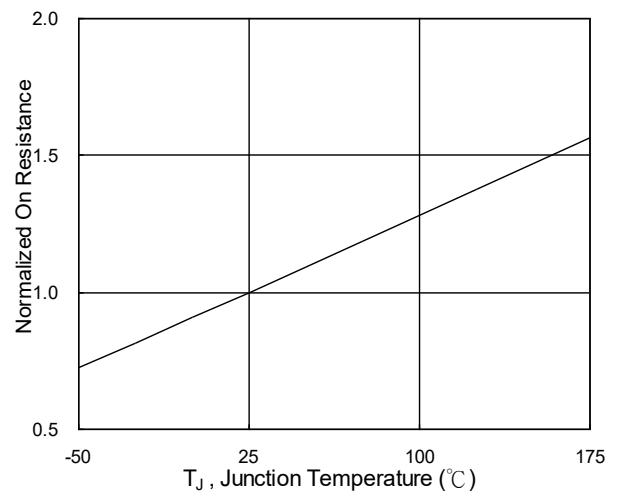


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

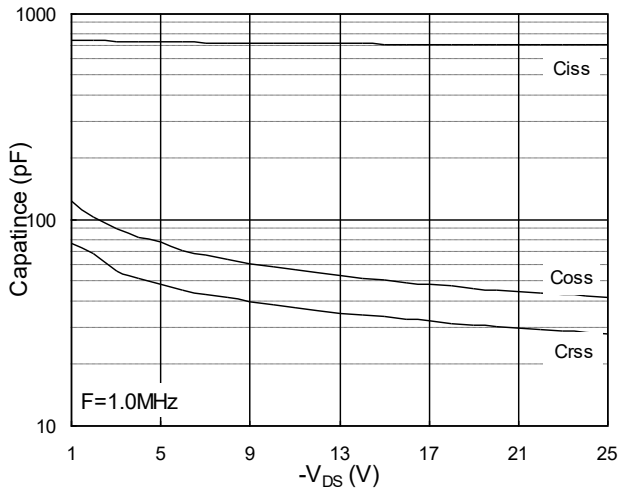


Fig.7 Capacitance

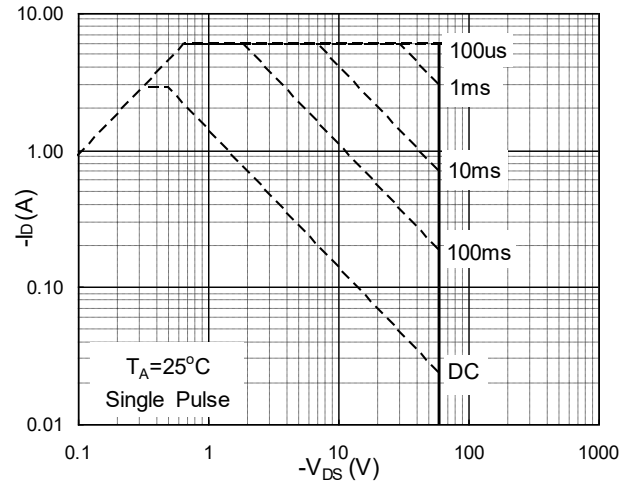


Fig.8 Safe Operating Area

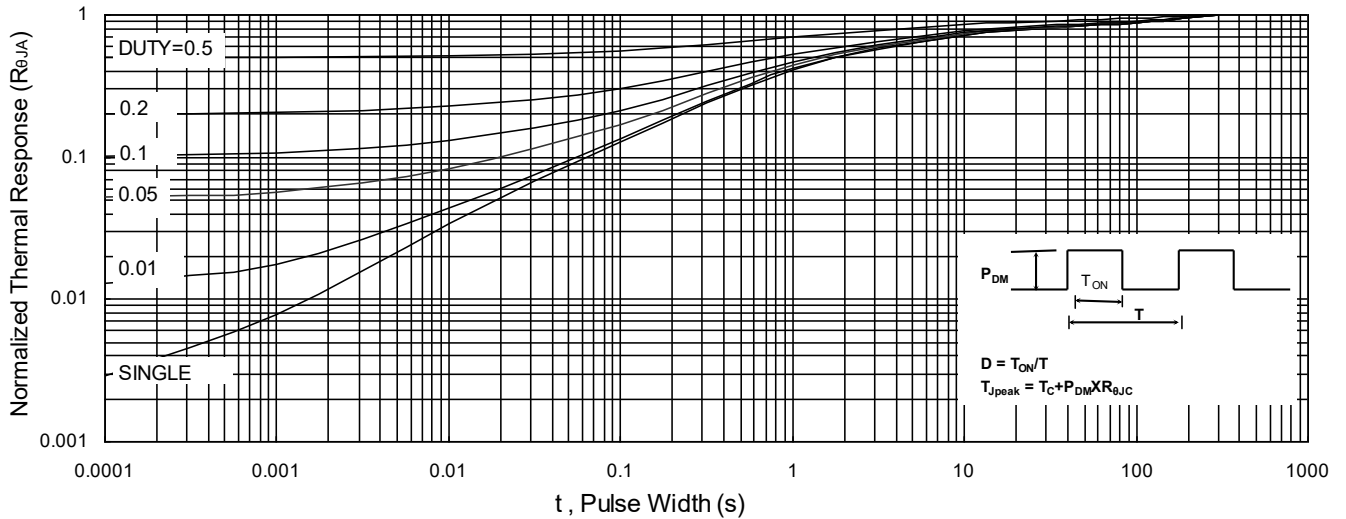


Fig.9 Normalized Maximum Transient Thermal Impedance

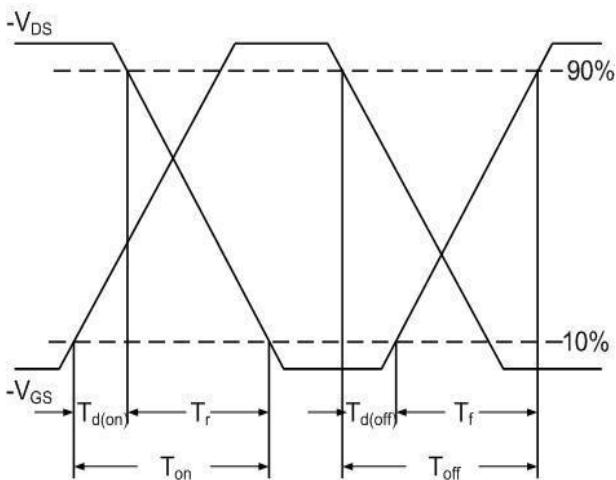


Fig.10 Switching Time Waveform

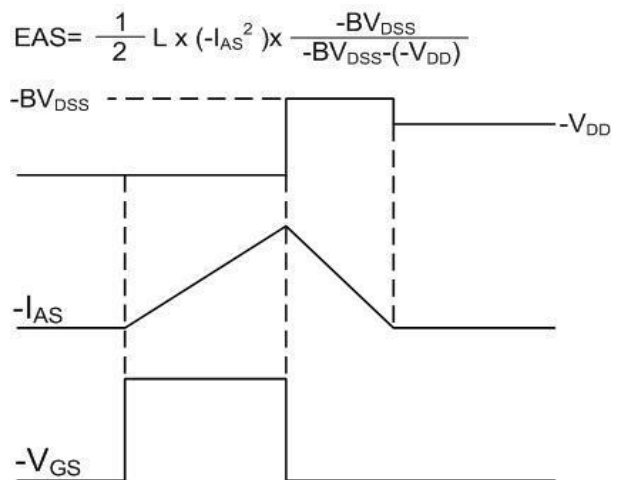


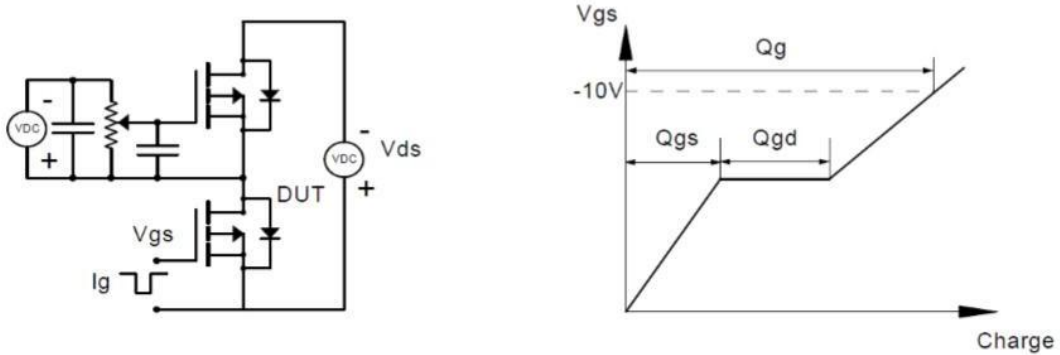
Fig.11 Unclamped Inductive Waveform

$$EAS = \frac{1}{2} L \times (-I_{AS}^2) \times \frac{-BV_{DSS}}{-BV_{DSS} - (-V_{DD})}$$

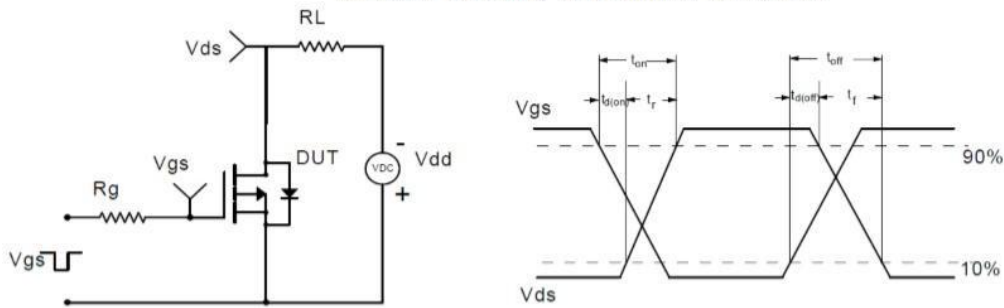


Test Circuit

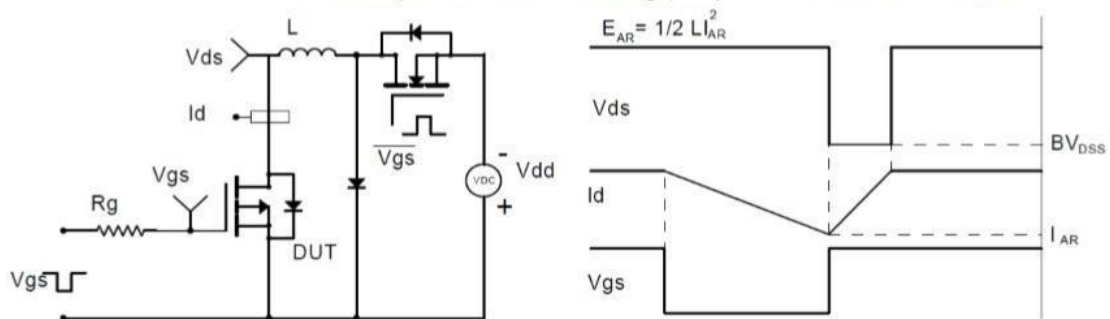
Gate Charge Test Circuit & Waveform



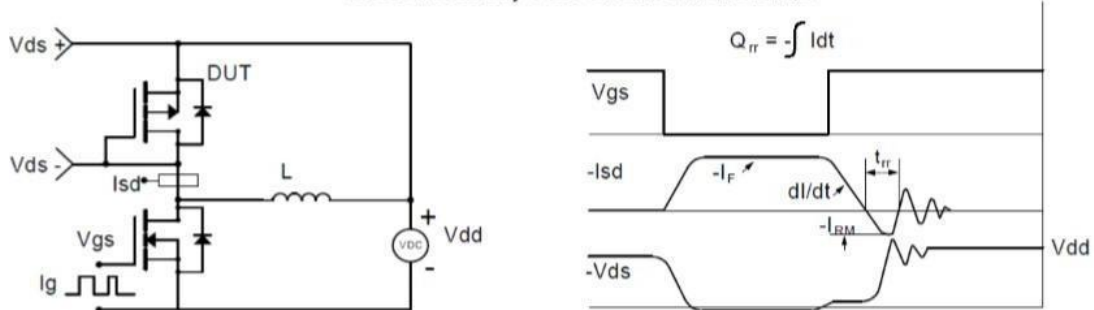
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

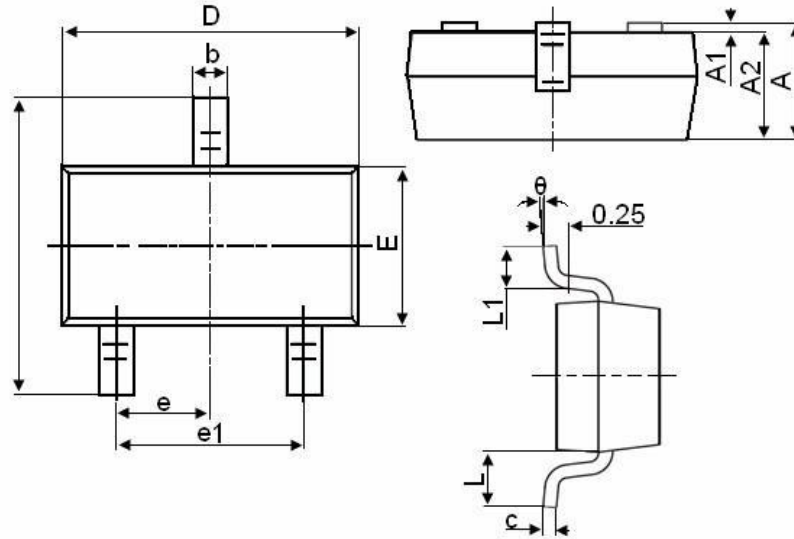


Diode Recovery Test Circuit & Waveforms





SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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